

Dual N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(m\Omega)(Typ.)$	I _D (A) ^a	Q _g (Typ.)			
20	450 at V _{GS} = 4.5 V	0.0	0.8 nC			
20	550 at V _{GS} = 2.5 V	0.6				

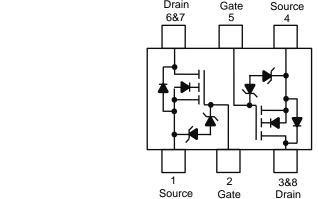
FEATURES

- DT-Trench Power MOSFET
- · RoHS Compliant
- Halogen Free

APPLICATIONS

- · Relay Driver
- · High-Speed Line Driver
- · Low-Side Load Switch
- · Switching Circuits

Drain



DFN1110-6A Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	20	V			
Gate-Source Voltage	V _{GS}	± 8	V			
Continuous Drain Current	T _A = 25 °C	I_	0.6			
Continuous Diam Current	T _A = 100 °C	I _D	0.4	А		
Pulsed Drain Current ^b	I _{DM}	2.5				
Maximum Power Dissipation ^c	T _A = 25 °C	PD	0.25	W		
iviaximum rower bissipation*	T _A = 100 °C		0.1	T vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	500	°C/W		
Junction-to-Case (Drain)	R _{thJC}	300			

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.5	-	1.0	V	
Gate-Body Leakage			-	-	± 10	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	-	-	1	μA	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	0.6	-	-	Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 0.5 \text{ A}$	-	450	600		
		V _{GS} = 2.5 V, I _D = 0.2 A	-	550	800	1	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 1.8 V, I _D = 0.1 A	-	750	1200	mΩ	
		V _{GS} = 1.5 V, I _D = 0.05 A	-	1200	-		
		V _{GS} = 1.2 V, I _D = 0.02 A	-	2500	-	1	
Dynamic ^b				•			
Input Capacitance	C _{iss}		-	60	-	pF	
Output Capacitance	Coss	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 MHz	-	9.3	-		
Reverse Transfer Capacitance	C _{rss}		-	7.3	-		
Total Gate Charge ^c	Q_g		-	0.8	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 0.6 \text{ A}$	-	0.11	-		
Gate-Drain Charge ^c	Q_{gd}		-	0.29	-		
Gate Resistance	R_g	f = 1 MHz	-	90	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	4.2	-	ns	
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V}, R_L = 20 \Omega, R_{GEN} = 6.2 \Omega,$	-	3.4	-		
Turn-Off Delay Time ^c	t _{d(off)}	Vgs = 4.5 V, I _D = 0.5 A	-	25.8	-		
Fall Time ^c	t _f		-	10.6	-		
Drain-Source Body Diode Ratings and Characteristics ^b (T _A = 25 °C)							
Continuous Source-Drain Diode Current	Continuous Source-Drain Diode Current I_S $T_C = 25 ^{\circ}C$		=	-	0.6	Α	
Pulsed Current	I _{SM}		-	-	2.5	Α	
Forward Voltagea	V_{SD}	$I_F = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.3	V	

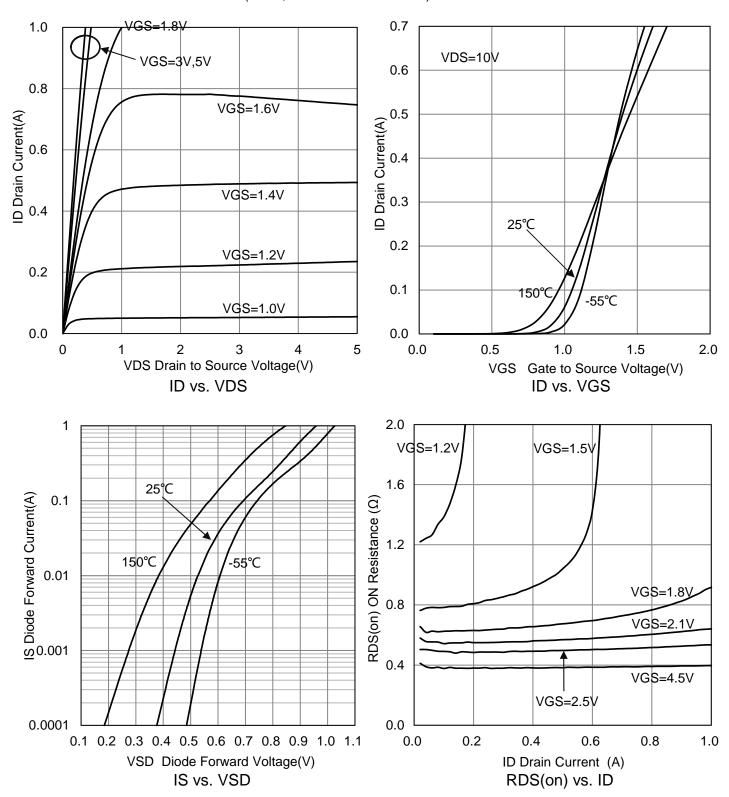
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

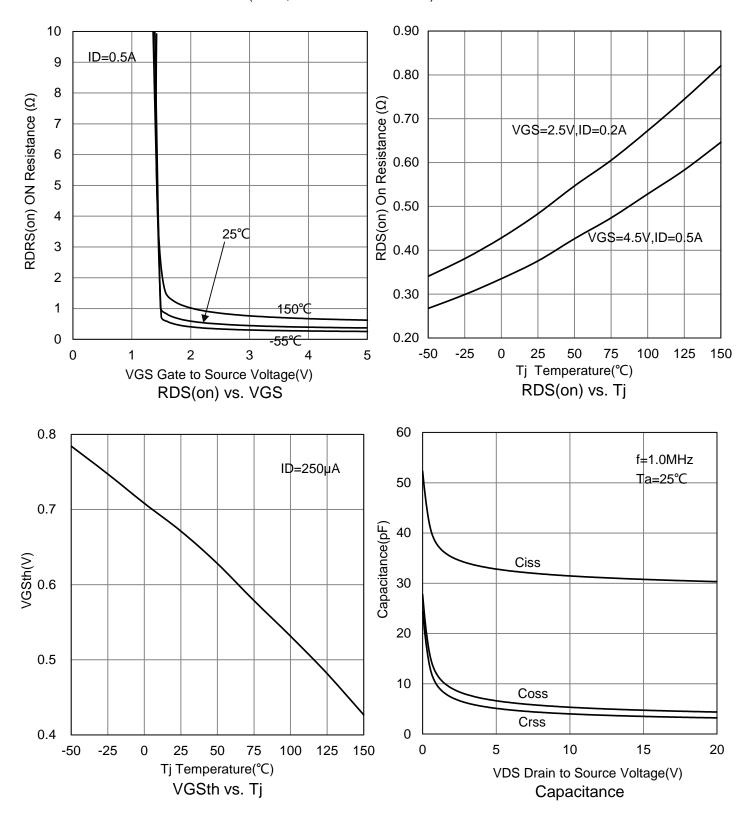
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

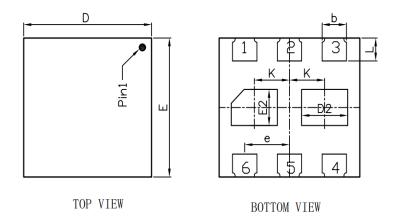


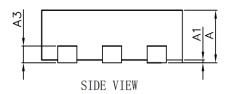
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)





DFN1110-6A PACKAGE OUTLINE





COMMON DIMENSIONS UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
Α	0.34	0.37	0.40
A1	0.01	0.02	0.04
b	0.15	0.19	0.23
L	0.125	0.165	0.205
D	1.05	1.10	1.15
Е	0.95	1.00	1.05
D2	0.32	0.36	0.40
E2	0.22	0.26	0.30
е	0.35		
A3	0.127 REF		
K	0.275		





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